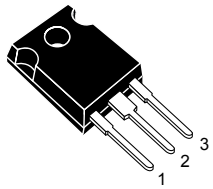
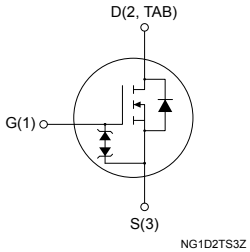
STW35N65DM2

Datasheet

N-channel 650 V, 93 mΩ typ., 32 A MDmesh DM2 Power MOSFET in a TO-247 package



TO-247



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STW35N65DM2	650 V	110 mΩ	32 A

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM2 fast-recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high-efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Product status link
STW35N65DM2

Product summary	
Order code	STW35N65DM2
Marking	35N65DM2
Package	TO-247
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage (static)	±25	V
	Gate-source voltage (AC, f > 1 Hz)	±30	
I_D	Drain current (continuous) at T_C = 25 °C	32	A
	Drain current (continuous) at T_C = 100 °C	20	
I_{DM} (1)	Drain current (pulsed)	90	A
P_{TOT}	Total power dissipation at T_C = 25 °C	250	W
dv/dt(2)	Peak diode recovery voltage slope	100	V/ns
di/dt(2)	Peak diode recovery current slope	1000	A/µs
dv/dt(3)	MOSFET dv/dt ruggedness	100	V/ns
T_{stg}	Storage temperature	-55 to 150	°C
T_J	Operating junction temperature		°C

1. *Pulse width is limited by safe operating area.*
2. *I_{SD} ≤ 32 A, V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 80% $V_{(BR)DSS}$.*
3. *V_{DS} ≤ 520 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.5	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_J max.)	4	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	1150	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	650			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 650 V			1	µA
		V_{GS} = 0 V, V_{DS} = 650 V, T_C = 125 °C(1)			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 16 A		93	110	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	2540	-	pF
C_{oss}	Output capacitance		-	115	-	pF
C_{rss}	Reverse transfer capacitance		-	2.5	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 520 V, V_{GS} = 0 V	-	204	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	4.2	-	Ω
Q_g	Total gate charge	V_{DD} = 520 V, I_D = 32 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	56.3	-	nC
Q_{gs}	Gate-source charge		-	12.7	-	nC
Q_{gd}	Gate-drain charge		-	27.6	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 325 V, I_D = 16 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	23.4	-	ns
t_r	Rise time		-	23	-	ns
$t_{d(off)}$	Turn-off delay time		-	72	-	ns
t_f	Fall time		-	10.4	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		32	A
I_{SDM} (1)	Source-drain current (pulsed)		-		90	A
V_{SD} (2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 32 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 32 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	100		ns
Q_{rr}	Reverse recovery charge		-	0.42		µC
I_{RRM}	Reverse recovery current		-	8.4		A
t_{rr}	Reverse recovery time	I_{SD} = 32 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_J = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	205		ns
Q_{rr}	Reverse recovery charge		-	1.8		µC
I_{RRM}	Reverse recovery current		-	17.6		A

1. *Pulse width is limited by safe operating area.*
2. *Pulse test: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

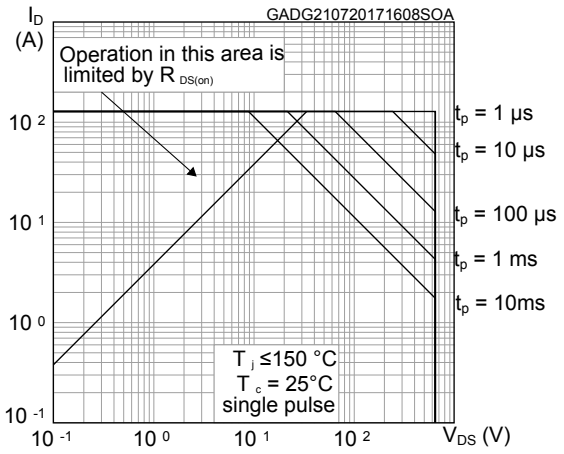


Figure 2. Thermal impedance

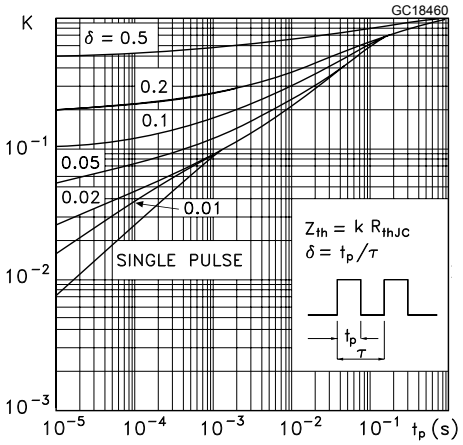


Figure 3. Output characteristics

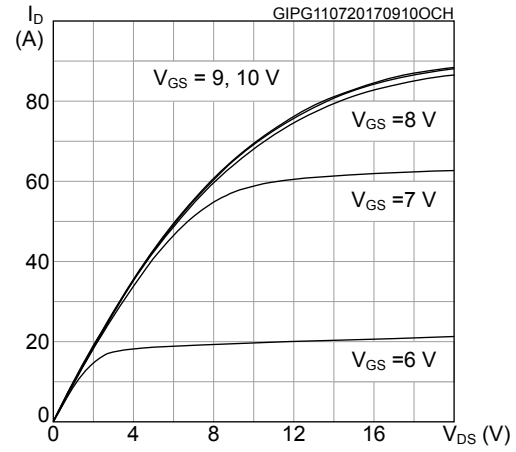


Figure 4. Transfer characteristics

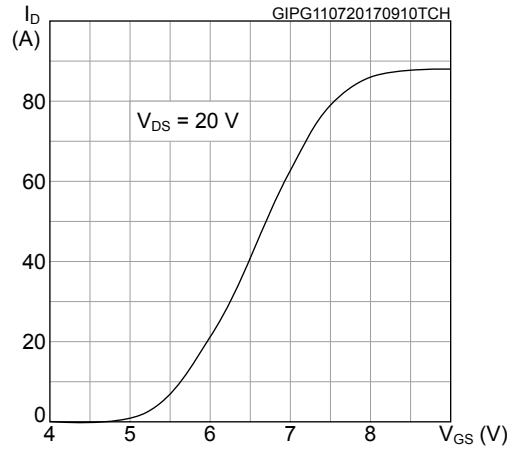


Figure 5. Gate charge vs gate-source voltage

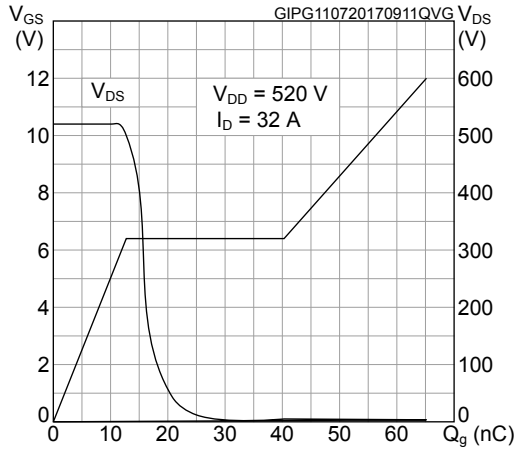


Figure 6. Static drain-source on-resistance

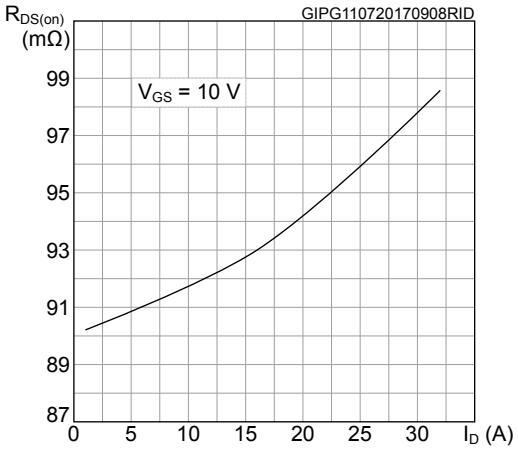


Figure 7. Capacitance variations

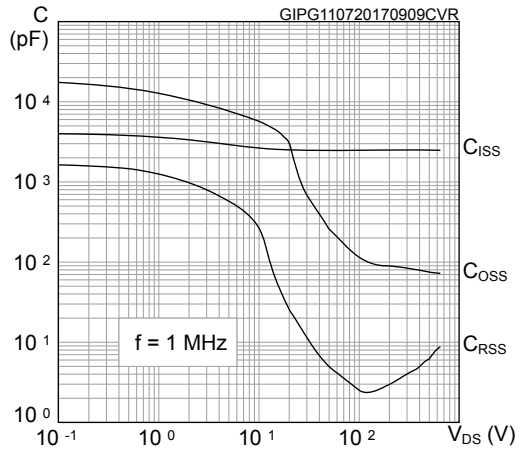


Figure 8. Normalized gate threshold voltage vs temperature

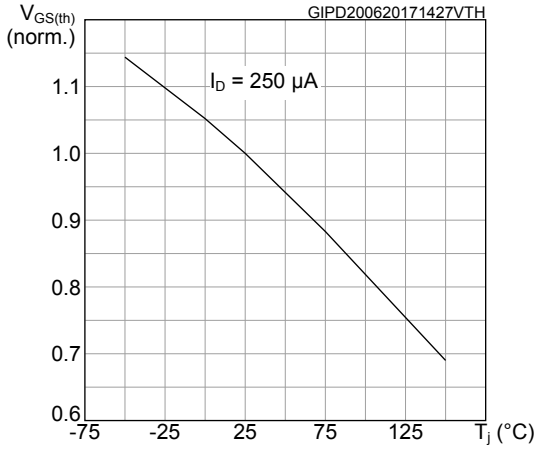


Figure 9. Normalized on-resistance vs temperature

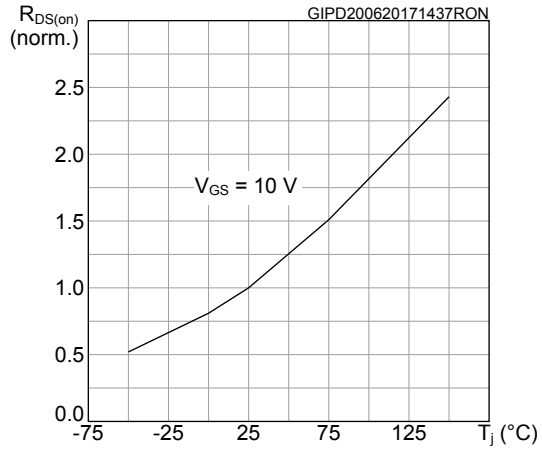


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

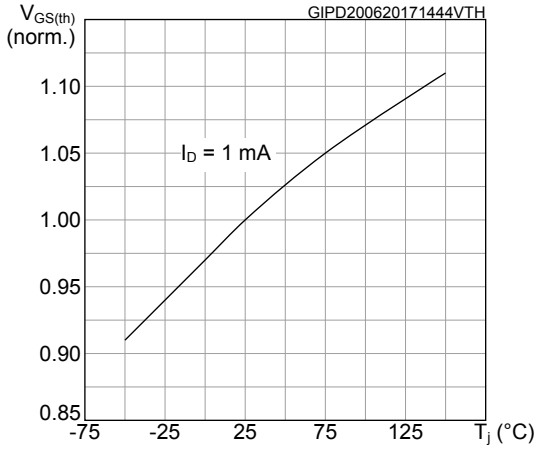


Figure 11. Output capacitance stored energy

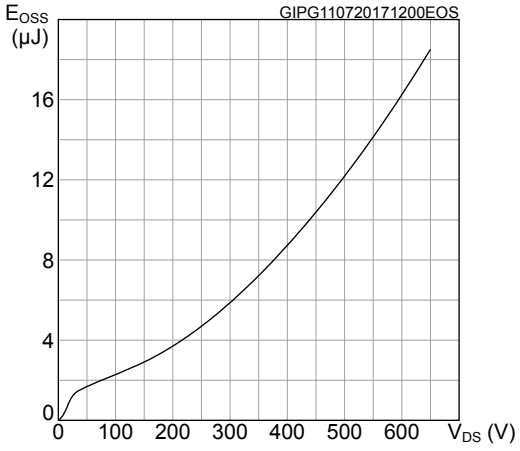
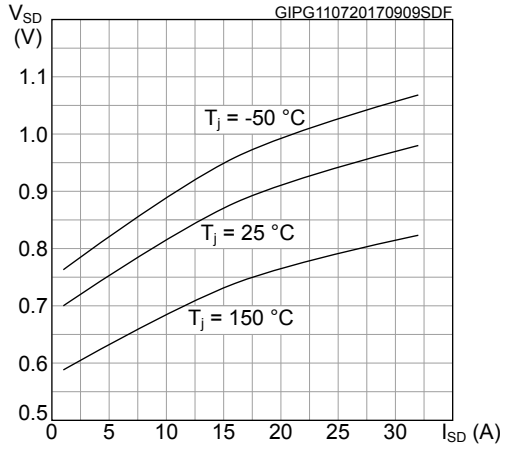
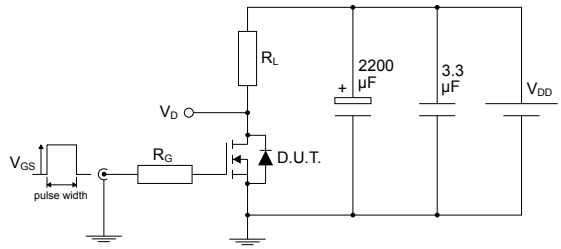


Figure 12. Source- drain diode forward characteristics



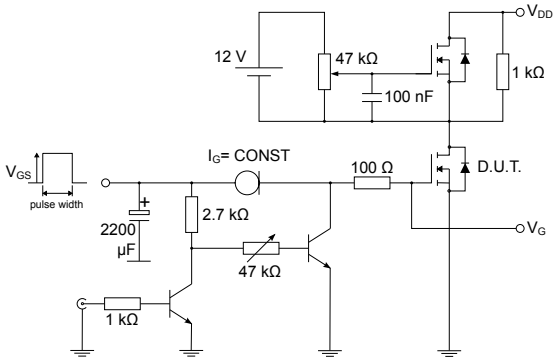
3 Test circuits

Figure 13. Test circuit for resistive load switching times



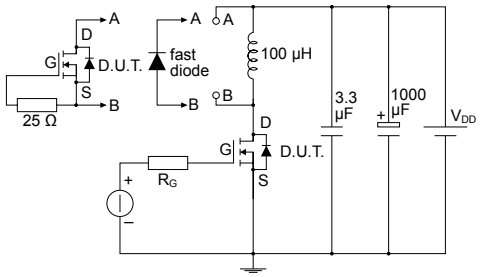
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Figure 14. Test circuit for gate charge behavior



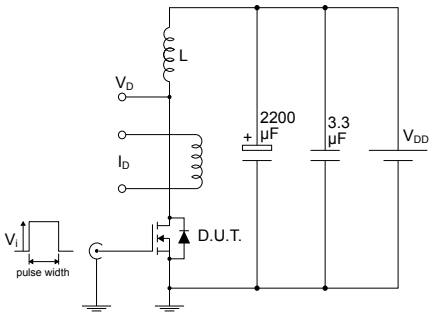
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Figure 15. Test circuit for inductive load switching and diode recovery times



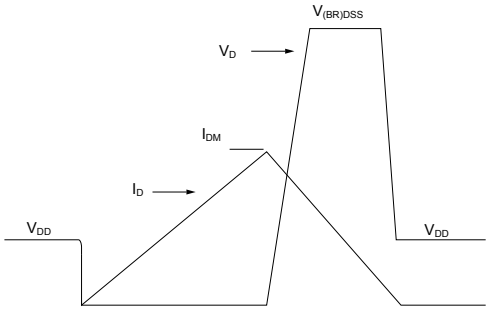
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Figure 16. Unclamped inductive load test circuit



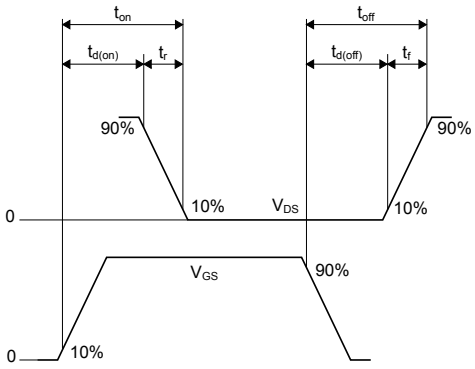
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Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



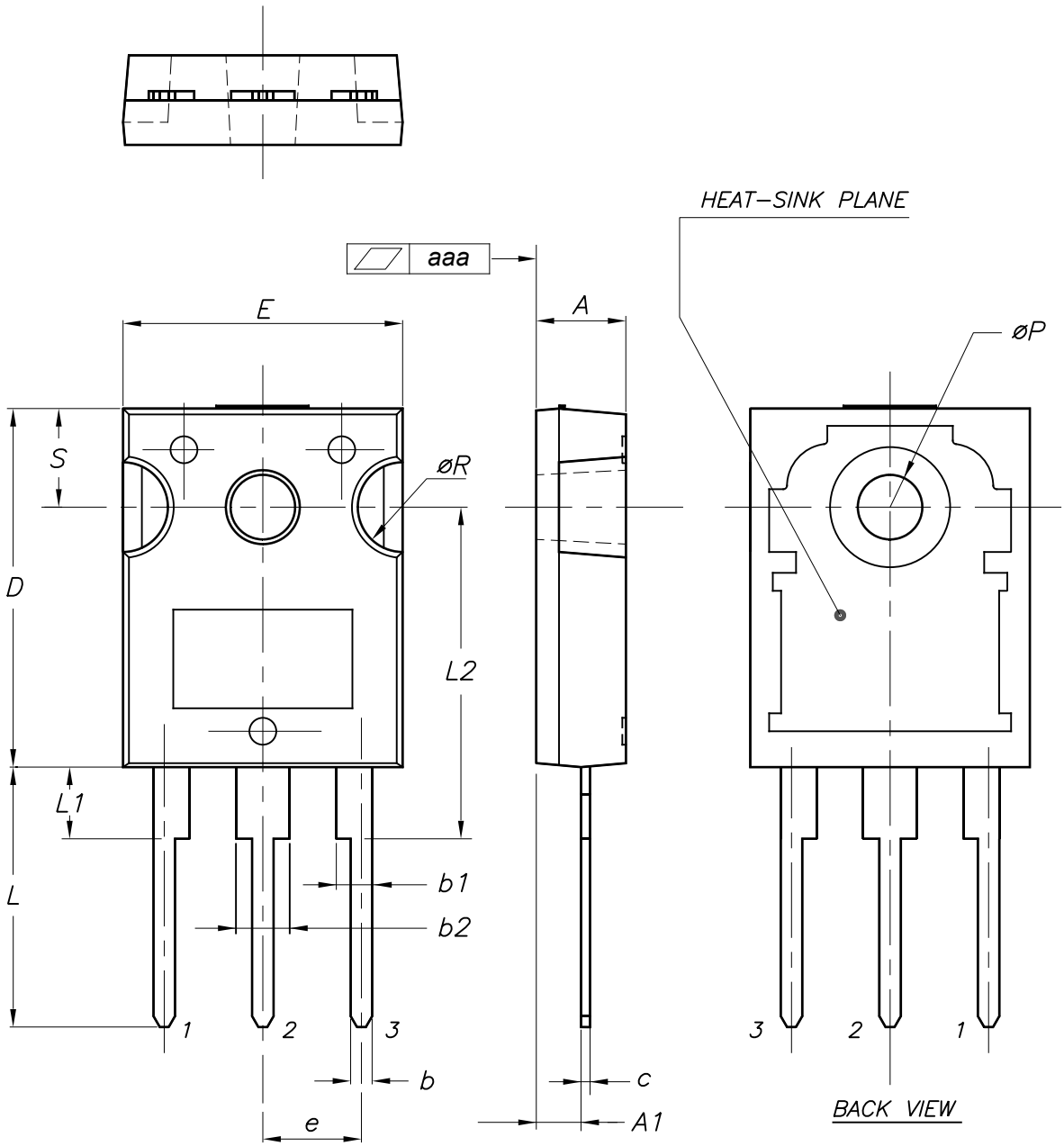
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 19. TO-247 package outline



0075325_10

Table 8. **TO-247 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70
aaa		0.04	0.10

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
21-Jul-2017	1	Initial release
12-Dec-2017	2	Document status change from preliminary data to production data. Update *Table 2: "Absolute maximum ratings"*, *Table 8: "Source-drain diode"* and *Figure 2: "Safe operating area"*. Minor text changes.
31-Aug-2020	3	Updated *Table 1. Absolute maximum ratings*. Minor text changes.
27-Oct-2023	4	Updated Figure 6. Static drain-source on-resistance. Updated Section 4.1 TO-247 package information. Minor text changes.

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